

MINI-MELF-SMD

LL4150
or
LL4150-1

Silicon Diode Switching

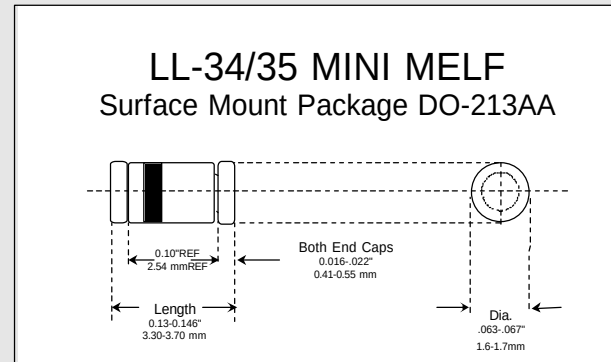
Applications

Used in general purpose applications, where a low current controlled forward characteristic and fast switching speed are important.

BKC can produce generic equivalents to JAN/ TX/ TXV and S level per MIL-S-19500/ 231 with internal source control drawings.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- Available in DO-35 package



Maximum Ratings

	Symbol	Value	Unit
Peak Inverse Voltage	PIV	75 (Min.)	Volts
Average Rectified Current	I_{Avg}	200	mAmps
Continuous Forward Current	I_{Fdc}	400	mAmps
Peak Surge Current ($t_{peak} = 1$ sec.)	I_{peak}	0.5	Amp
BKC Power Dissipation $T_L = 50^\circ C$, $L = 3/8"$ from body	P_{tot}	500	mWatts
Operating Temperature Range	T_{Op}	-65 to +200	$^\circ C$
Storage Temperature Range	T_{St}	-65 to +200	$^\circ C$

Electrical Characteristics @ 25°C	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ $I_F = 1.0$ mA	V_F	0.54	0.62	Volts
Forward Voltage Drop @ $I_F = 10$ mA	V_F	0.66	0.74	Volts
Forward Voltage Drop @ $I_F = 50$ mA	V_F	0.76	0.86	Volts
Forward Voltage Drop @ $I_F = 100$ m	V_F	0.80	0.92	Volts
Forward Voltage Drop @ $I_F = 200$ mA	V_F	0.87	1.0	Volts
Reverse Leakage Current @ $V_R = 50$ V	I_R		0.1 (100 @ 150 $^\circ C$)	μA
Breakdown Voltage @ $I_R = 0.1$ mA	PIV	75		Volts
Capacitance @ $V_R = 0$ V, $f = 1$ MHz	C_T		2.5	pF
Reverse Recovery time (note 1)	t_{rr}		4.0	nSecs
Reverse Recovery time (note 2,3)	t_{rr}		6.0	nSecs
Forward Recovery time (note 4)	V_{fr}		10	nSecs

Note 1: Per Method 4031-A with $I_F = I_R = 10$ to 200 mA, $R_L = 100$ Ohms, recover to 0.1 If.

Note 2: Per Method 4031-A with $I_F = I_R = 200$ to 400 mA, $R_L = 100$ Ohms, recover to 0.1 If.

Note 3: Per Method 4031-A with $I_F = 10$ microA, $I_R = 1.0$ mA, recover to 0.1 mA.

Note 4: Per Method 4026 with $I_F = 200$ mA, $I_R = 1.0$ mA, recover to 0.1 mA.



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